

Toward a gated FET on the basis of spin-transition polymers

*S. V. Andreev and S. Burdin
University of Bordeaux, LOMA (CNRS)*

We present a theoretical model of spin transitions in stacks of molecular layers. Our model captures the already established physics of these systems (thermal hysteretic crossovers and transitions) and suggests a way towards in situ control of this physics by means of external fields applied to the boundary layer. Our results pave the way toward both temperature and voltage controllable organic memory.